

# **Highly Interleaved 5b 250MS/s ADC with Redundant Channels in 65nm CMOS**

Brian P. Ginsburg<sup>1</sup> and  
Anantha P. Chandrakasan<sup>2</sup>

<sup>1</sup>Texas Instruments,

<sup>2</sup>Massachusetts Institute of Technology

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# Outline

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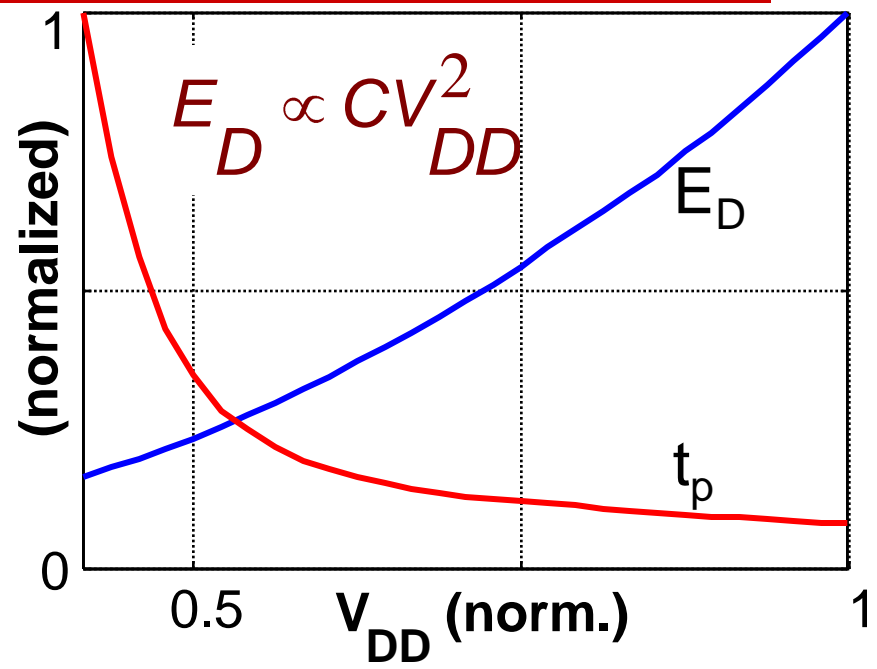
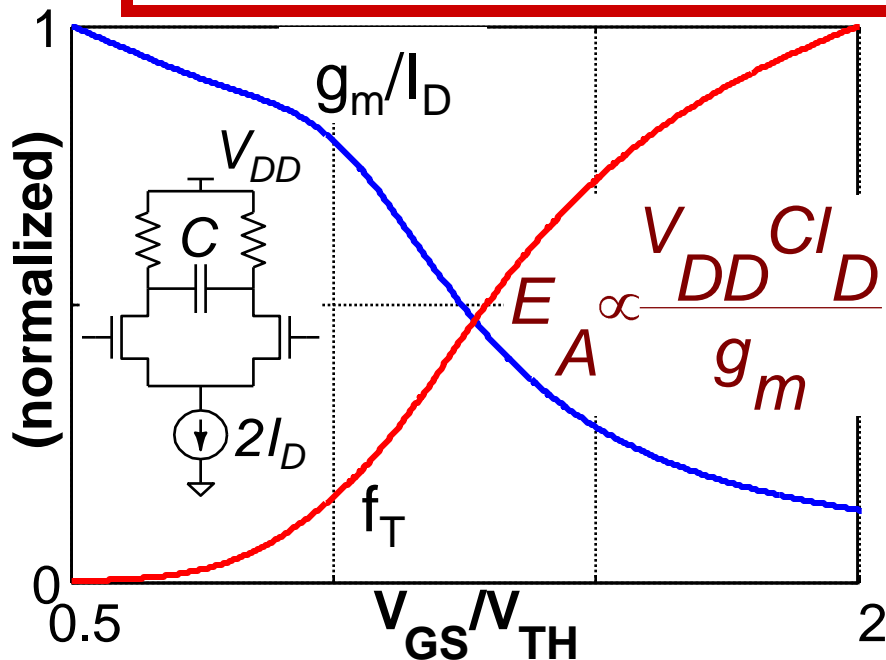
- Parallelism in ADCs
- Local Variation and Redundancy
- Chip Implementation
- Measured Results
- Variation and Yield Data
- Conclusions

# Why Time-Interleave?

- Push resolution/speed boundary of an architecture [Poulton, ISSCC 2003], [Draxelmayr, ISSCC 2004]

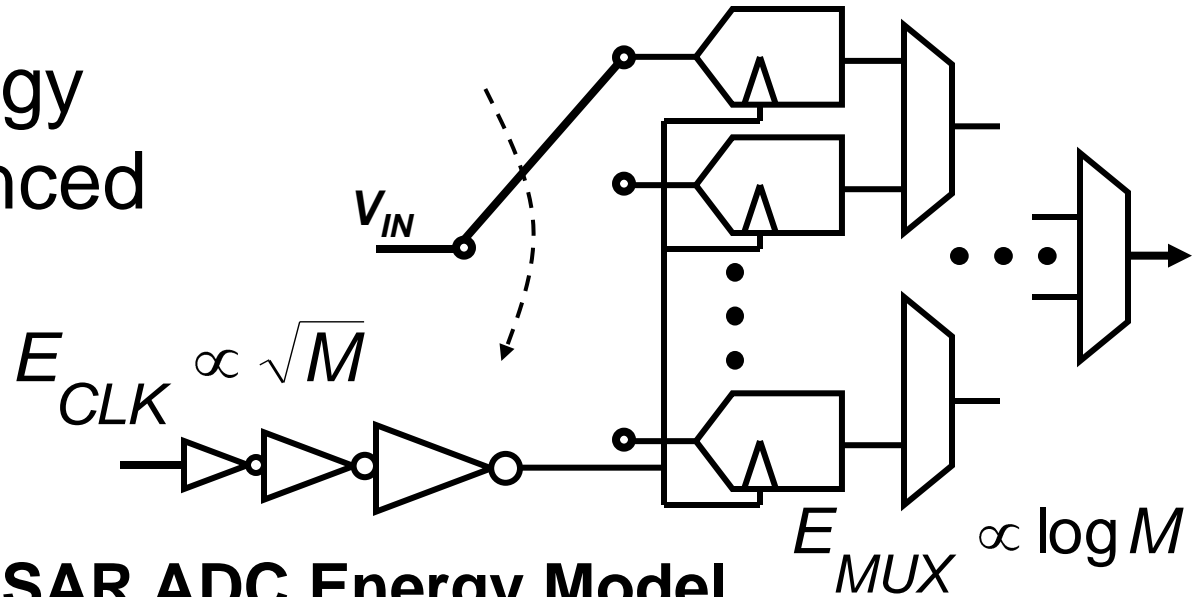
Slower ADCs are more energy efficient

- Analog circuits biased in sub-threshold
- Reduced digital supply voltages

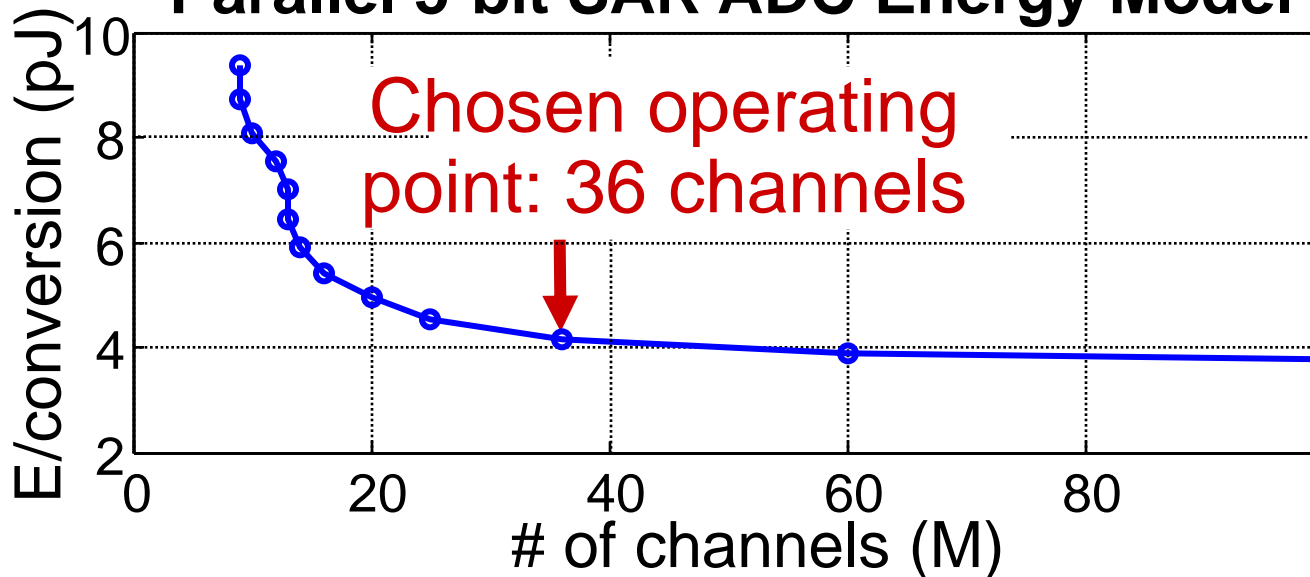


# Parallelism and Energy

Per-channel energy advantages balanced by overheads of parallelism

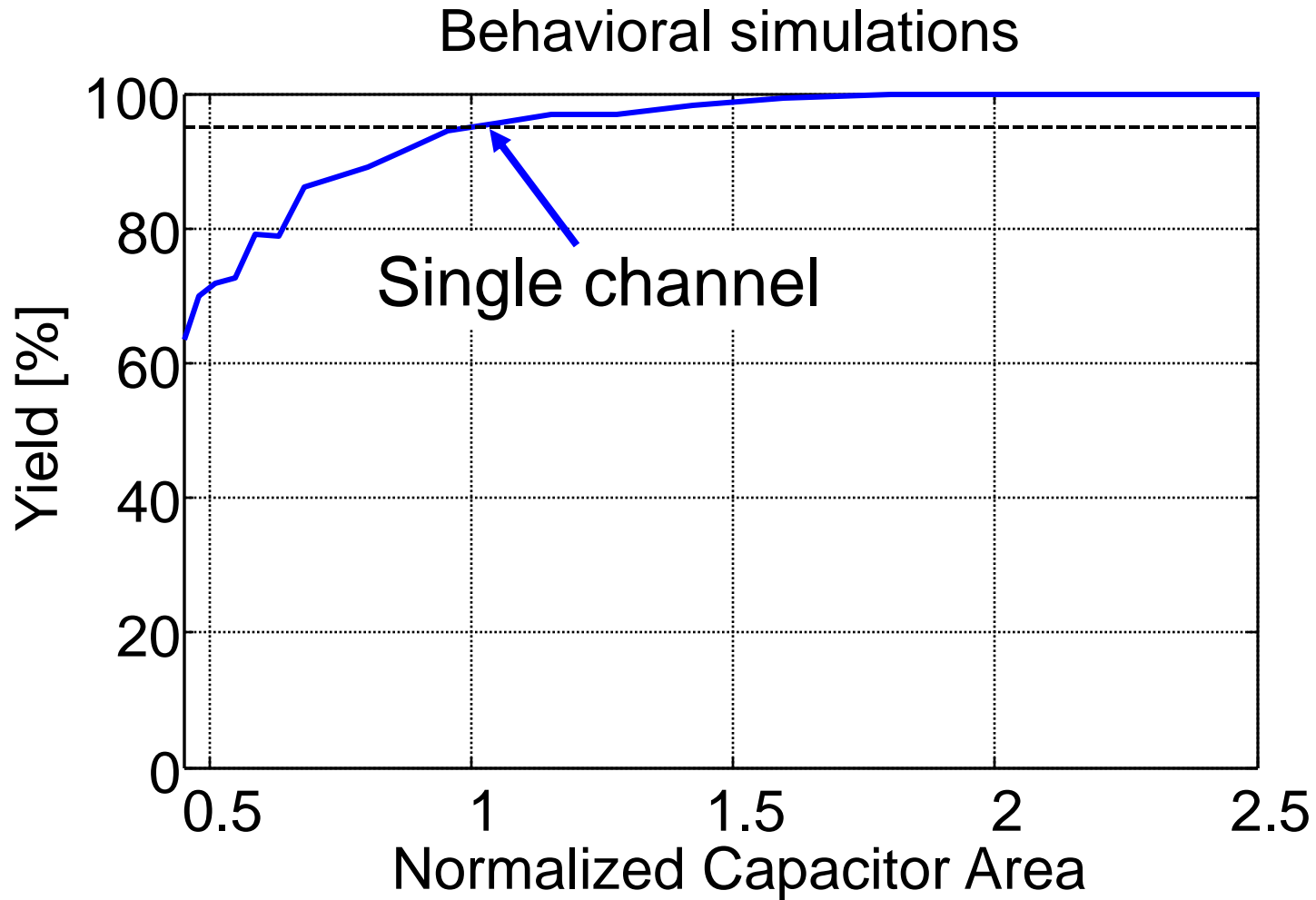


Parallel 5-bit SAR ADC Energy Model

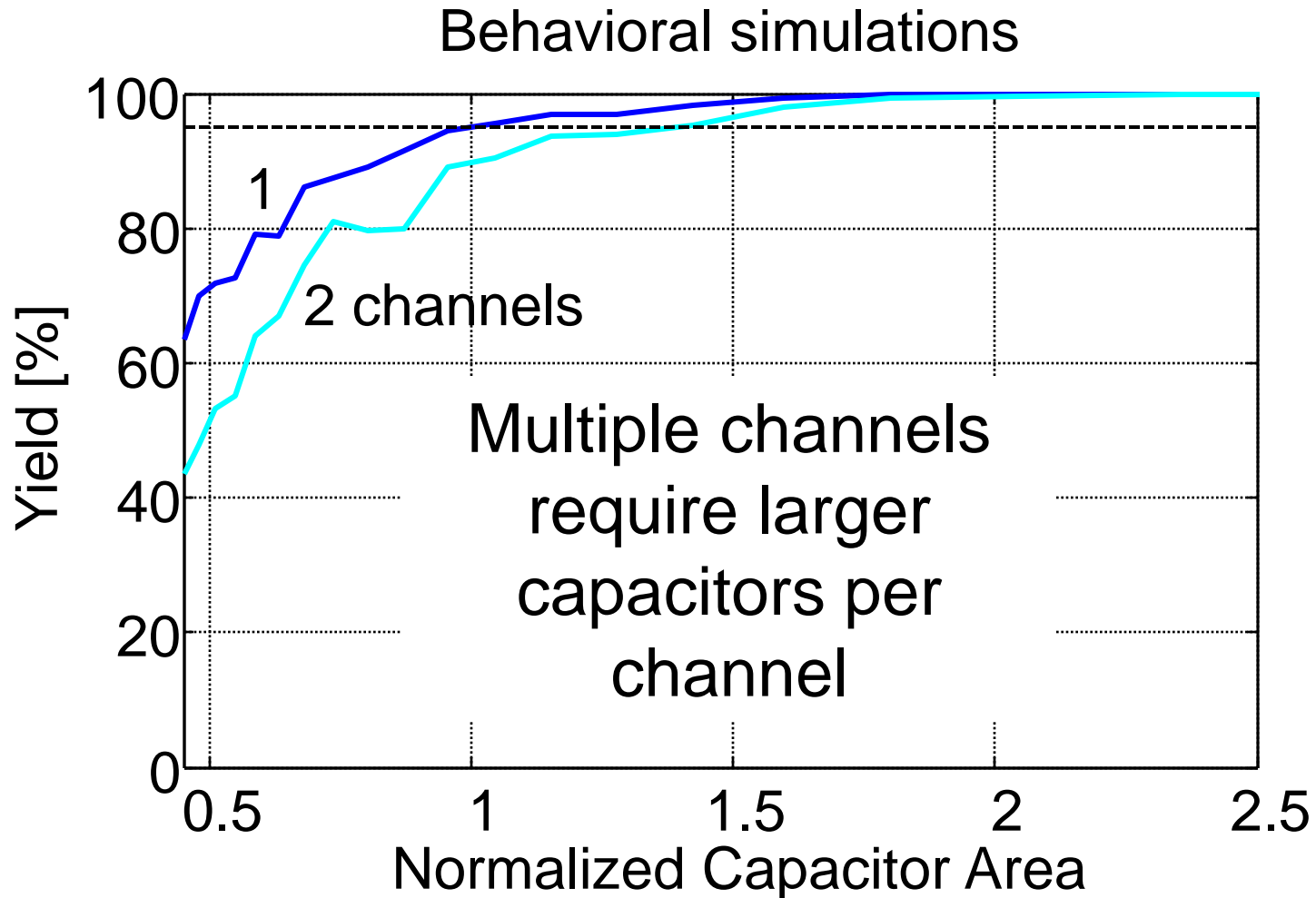


M = # of channels

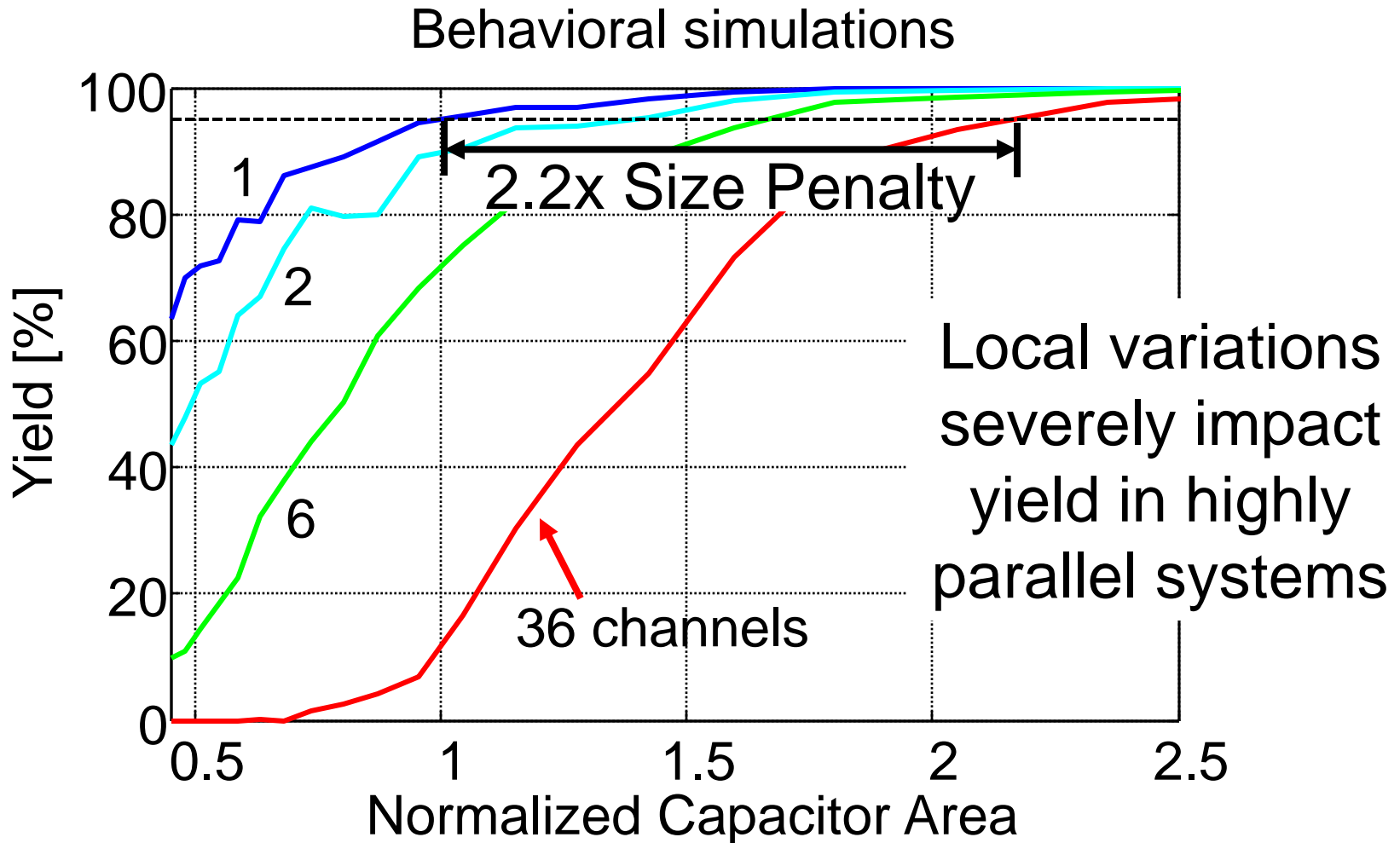
# Capacitor Sizing and Yield



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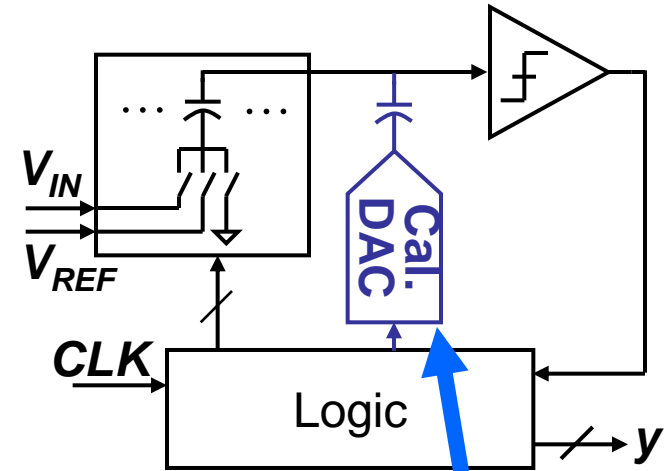
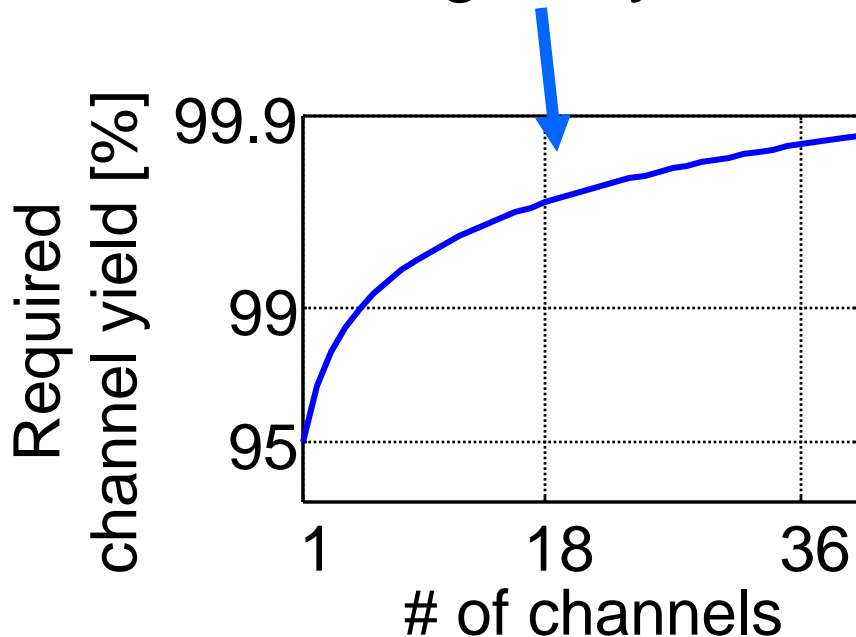


# Capacitor Sizing and Yield



# Mitigating Local Variation

- Calibration is the standard solution to improve yield [Poulton, ISSCC 2003]
- Final required channel yield is unchanged by calibration



Corrects for INL, DNL, & OS

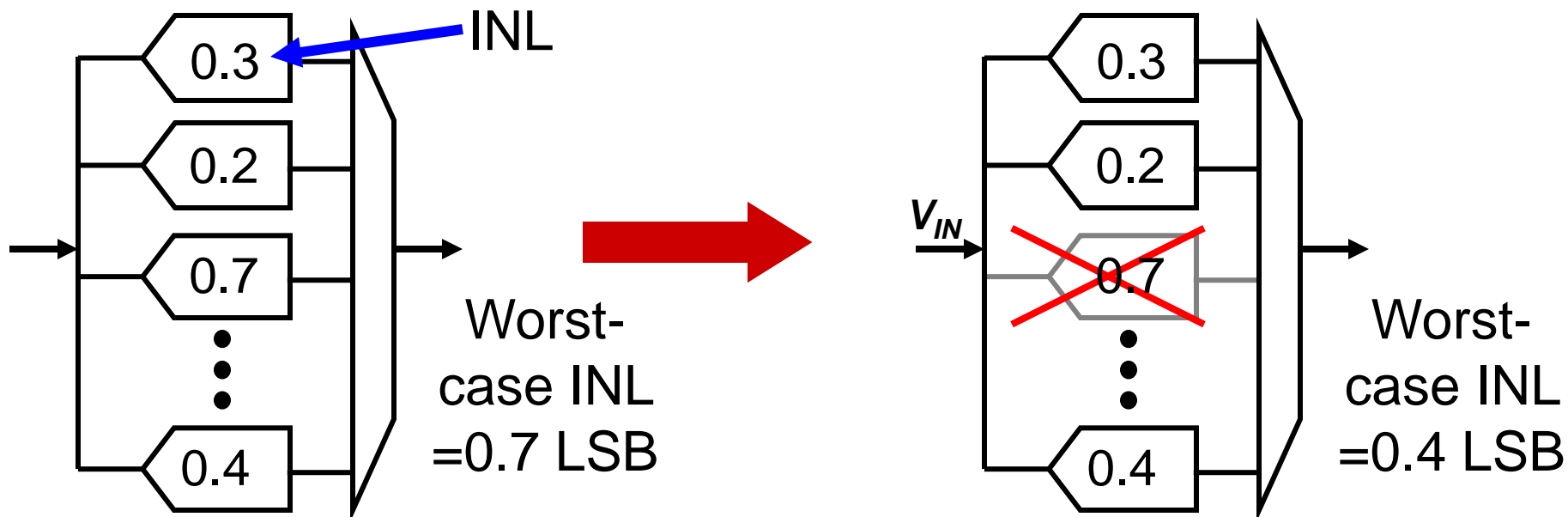
Fault coverage is limited by particular calibration choice



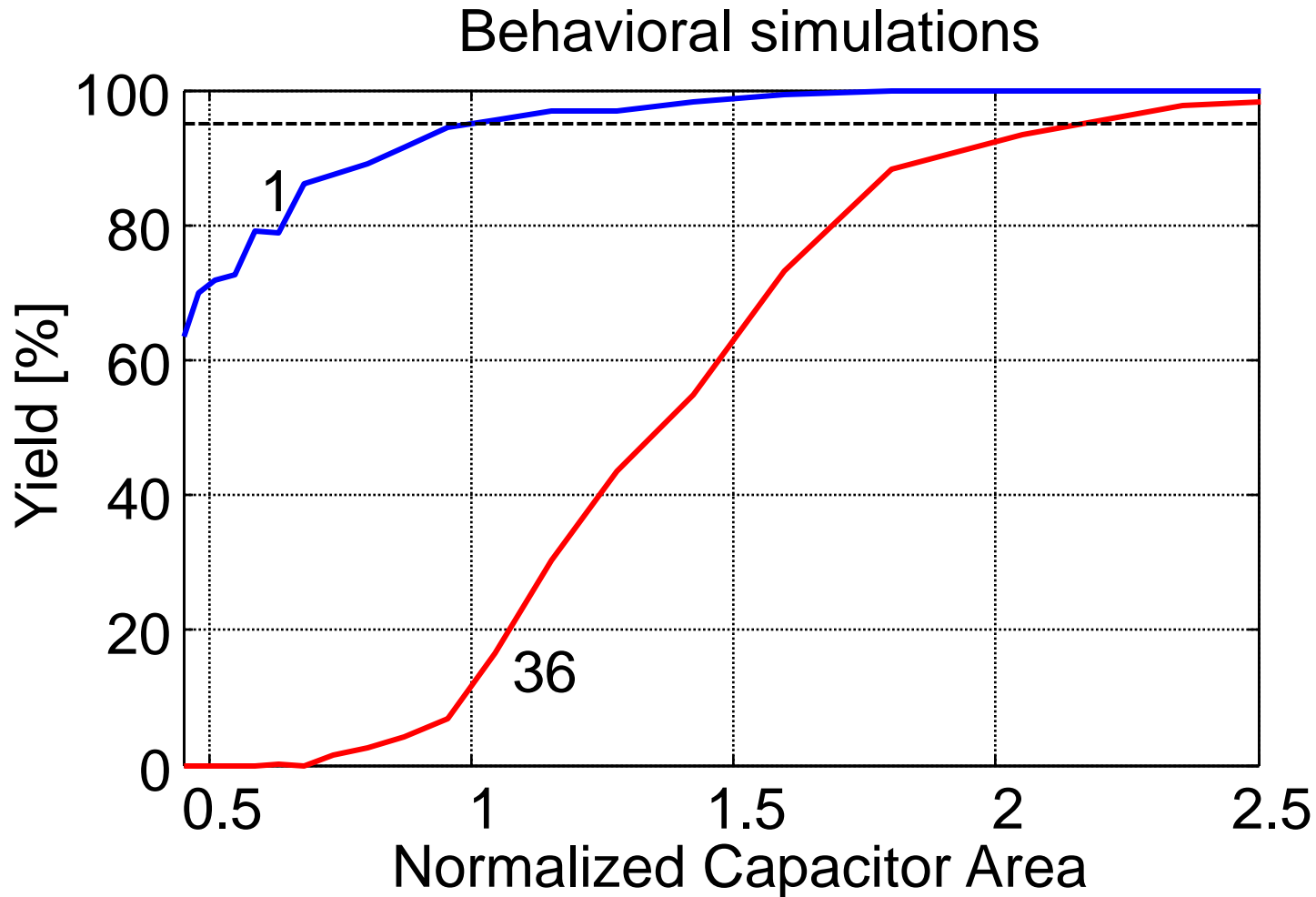
# Redundancy

Adding extra (redundant) channels addresses the underlying statistics

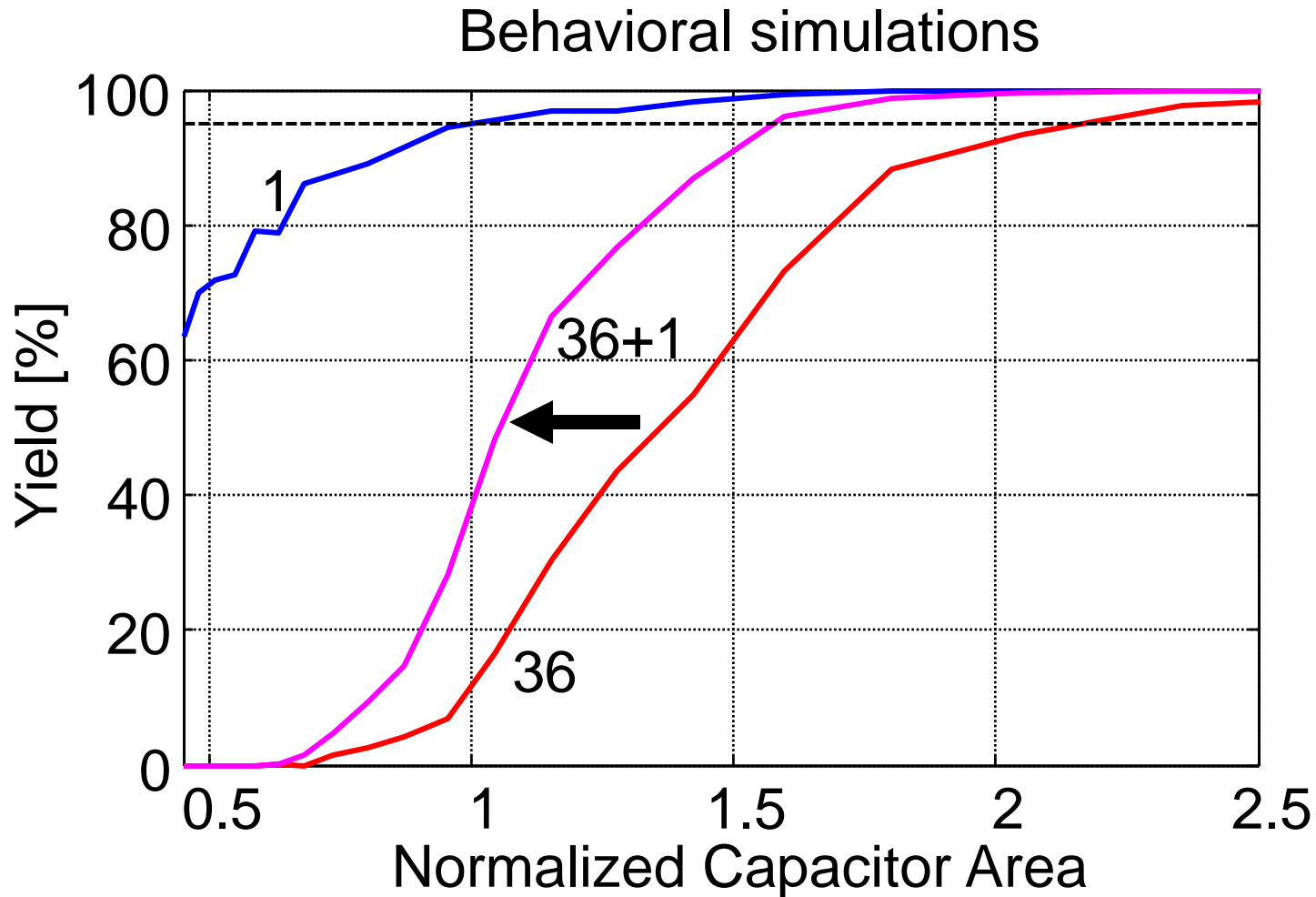
- Apply redundancy at maximum level of parallelism
- Eliminate the “worst” channels that otherwise limit yield



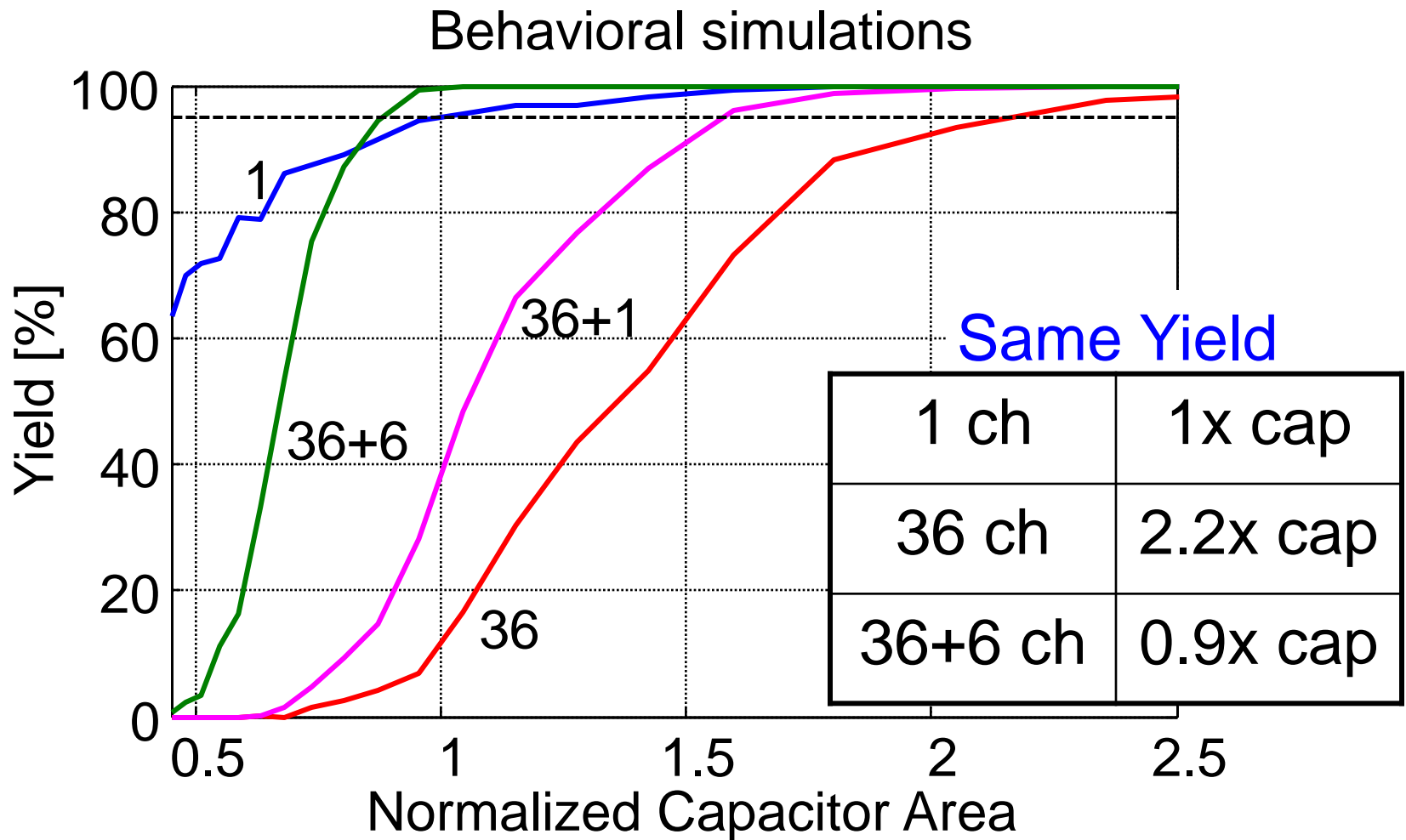
# Capacitor Sizing + Redundancy



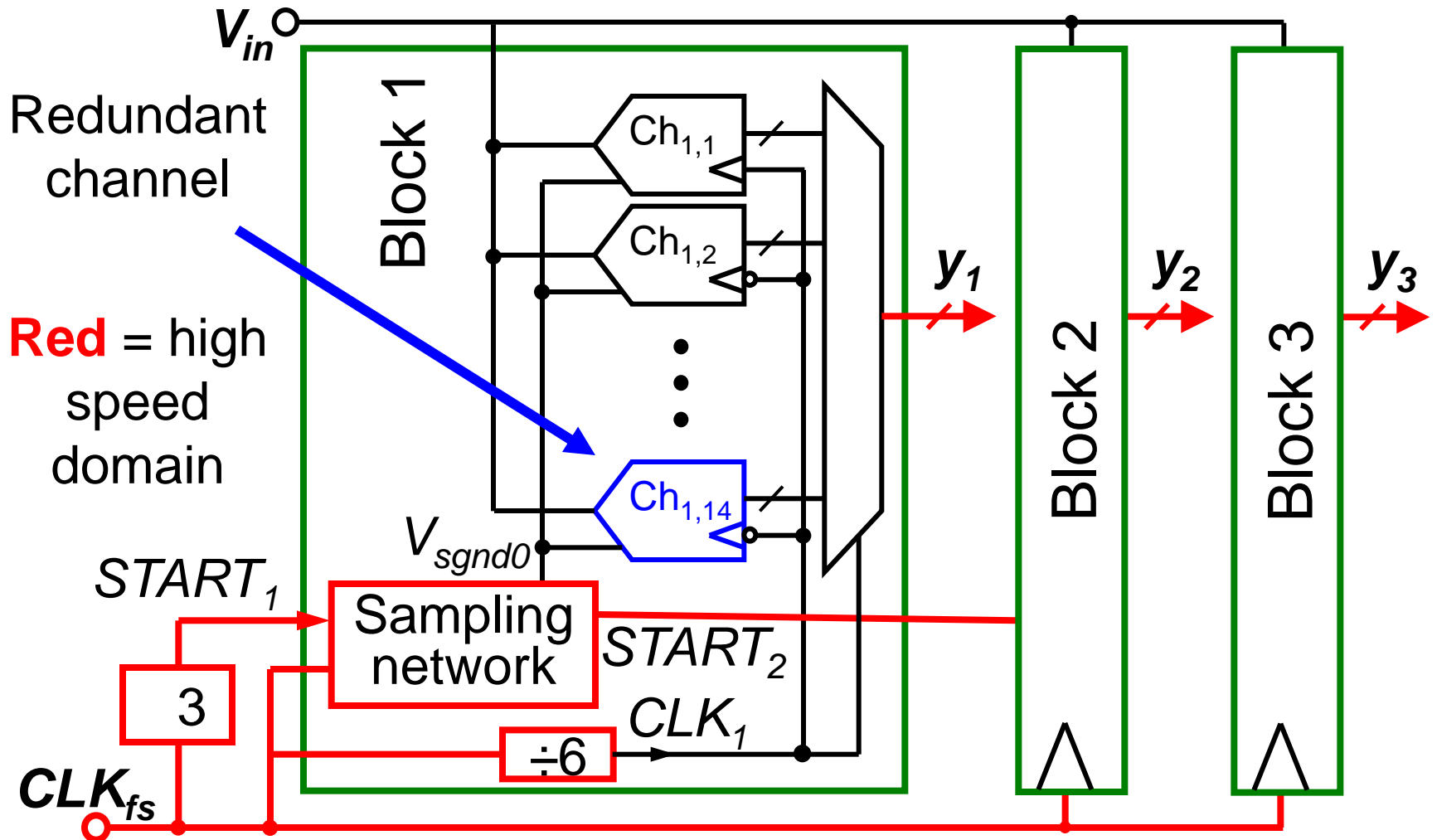
# Capacitor Sizing + Redundancy



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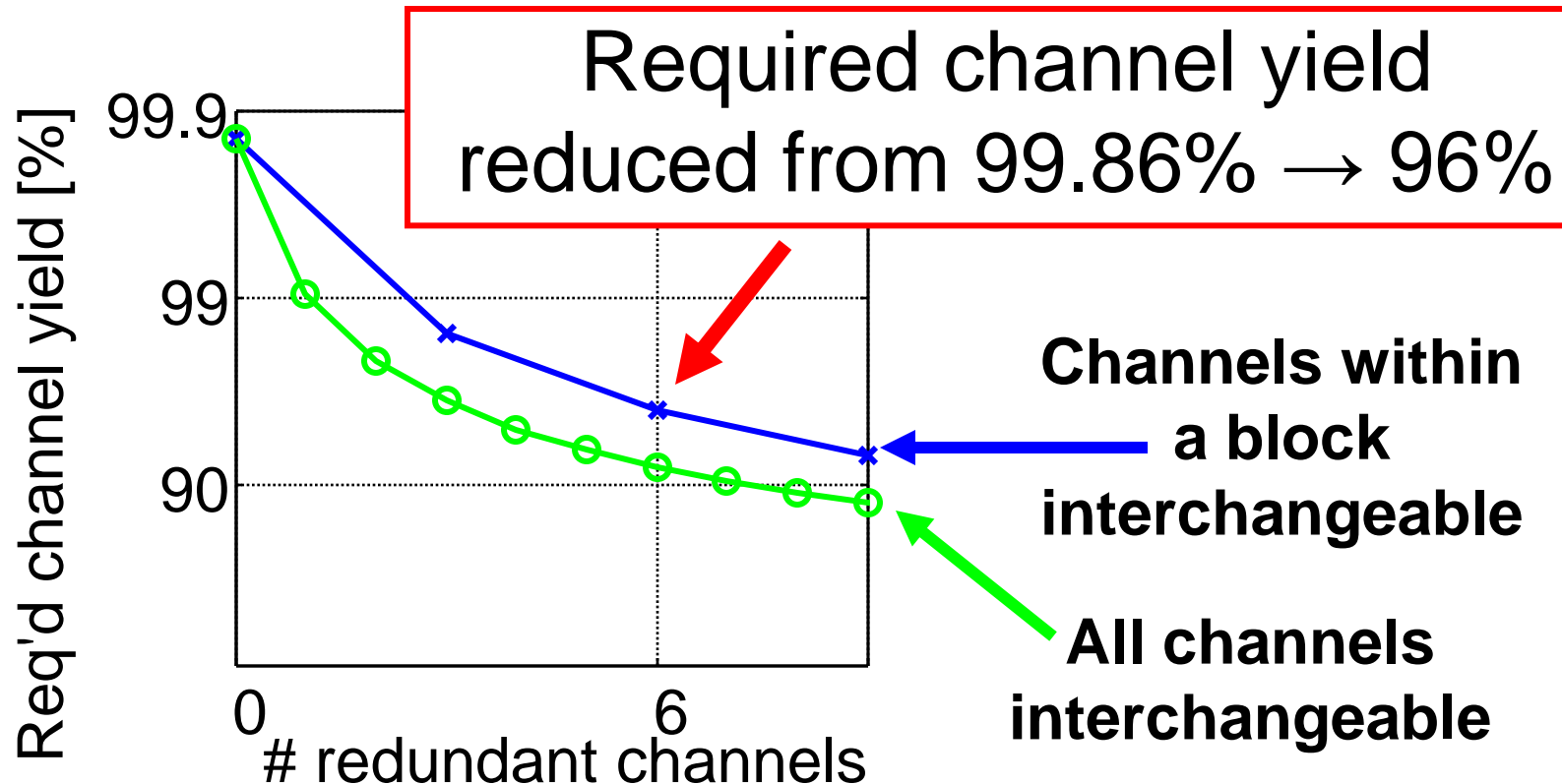


# ADC Block Diagram



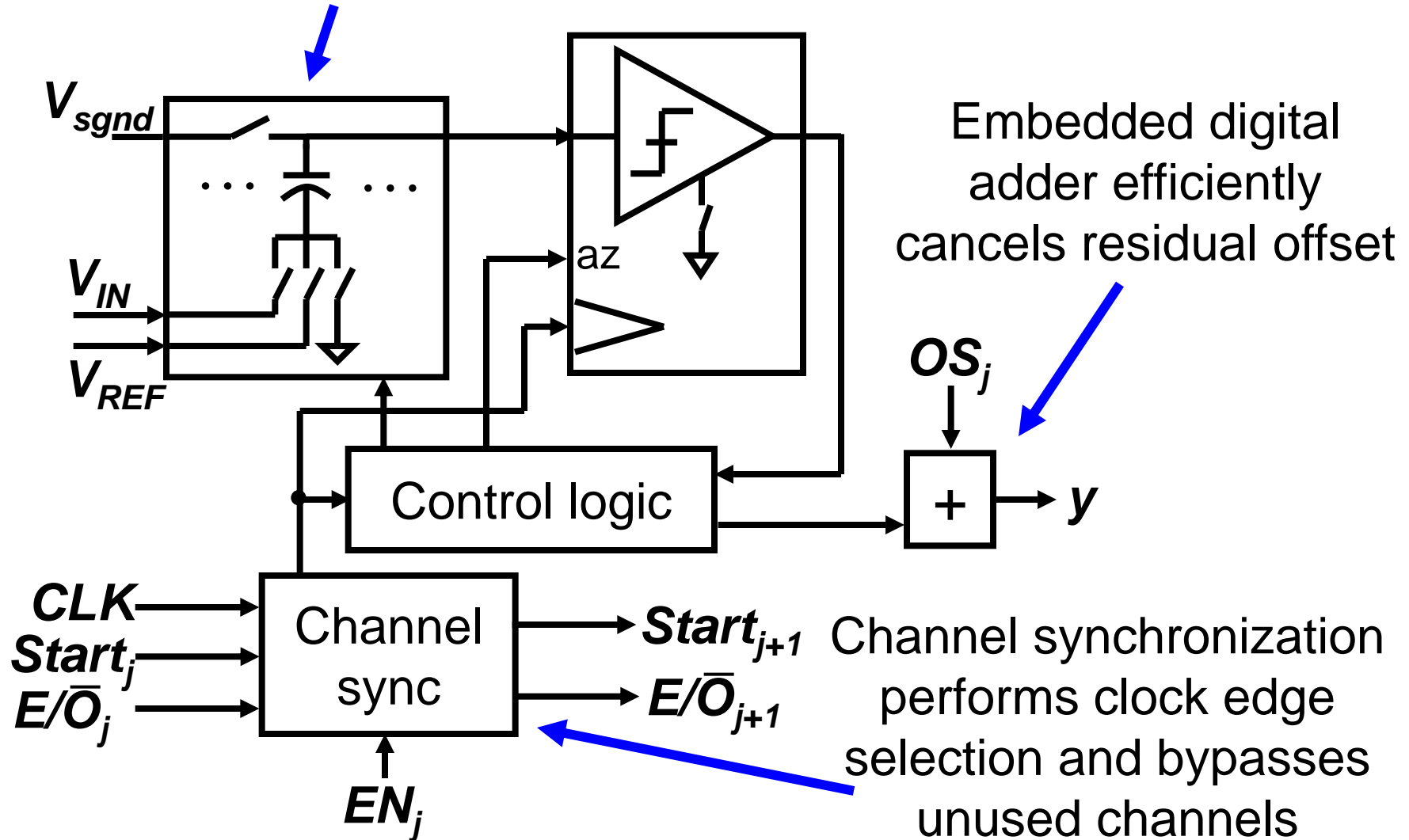
# Redundancy and Yield

- Generalization: redundant channels reduce required channel yield for a given overall yield (95%)

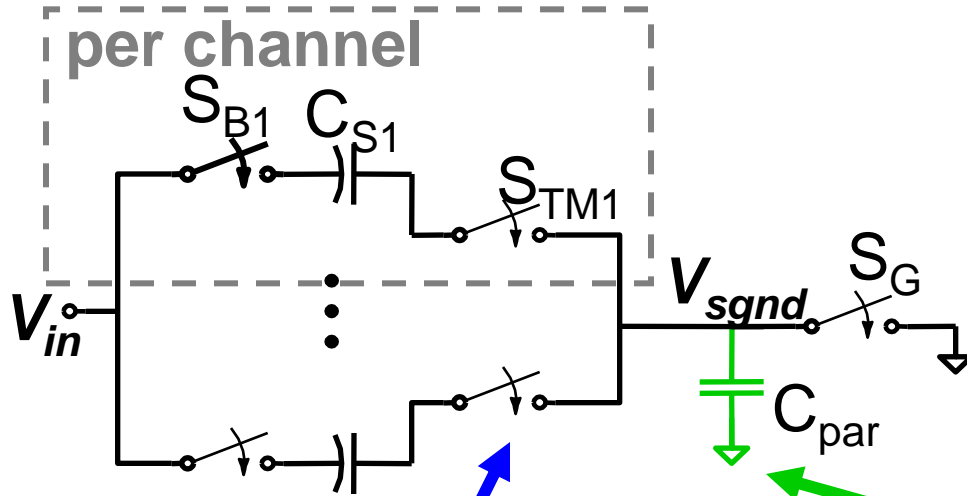


# SAR Channel Implementation

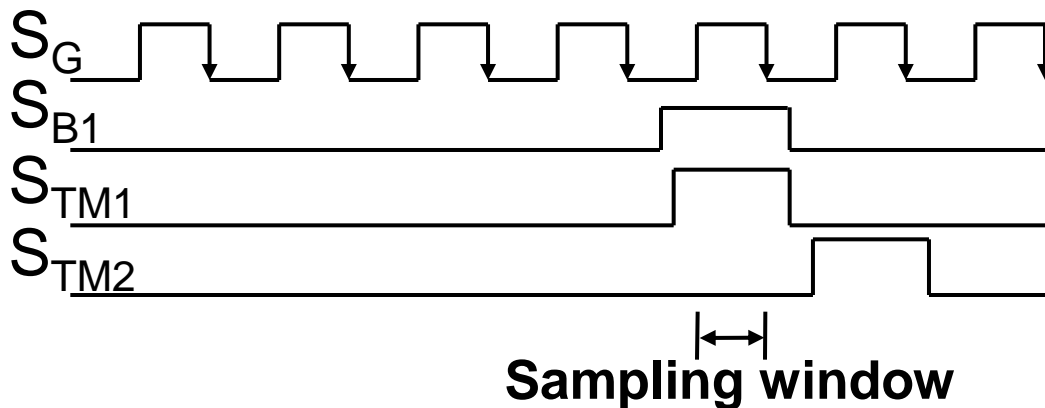
Split capacitor array [Ginsburg, JSSC 4/07]



# Global Sampling Network



**Top-plate switches smaller than bottom-plate**

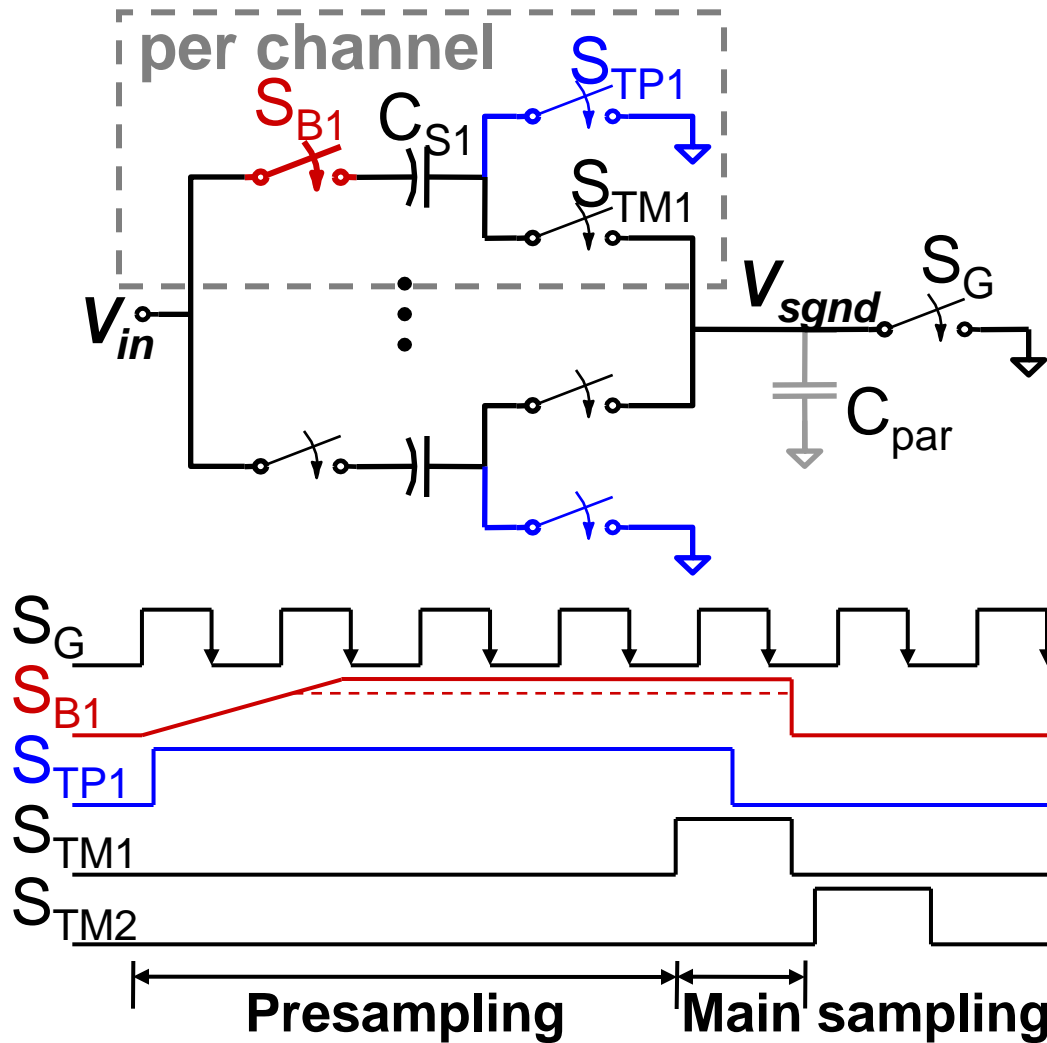


Timing skew minimized by a global switch [Gustavsson, TCAS-II, 9/00] that defines all sampling instants.

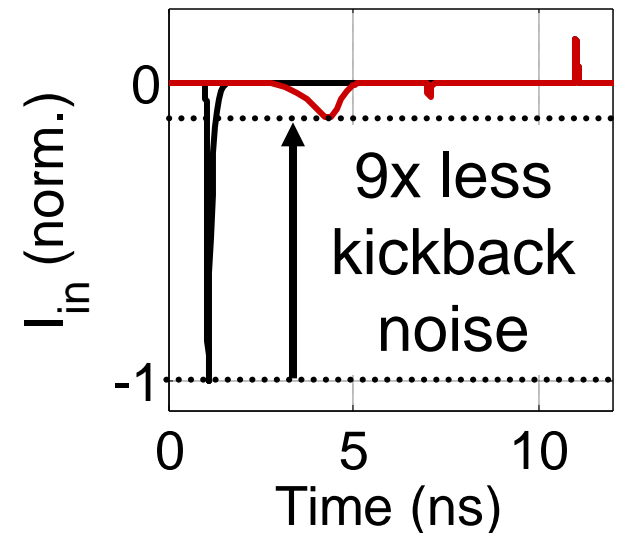
Block structure reduces parasitic capacitance that causes residual skew



# Extended Sampling Network

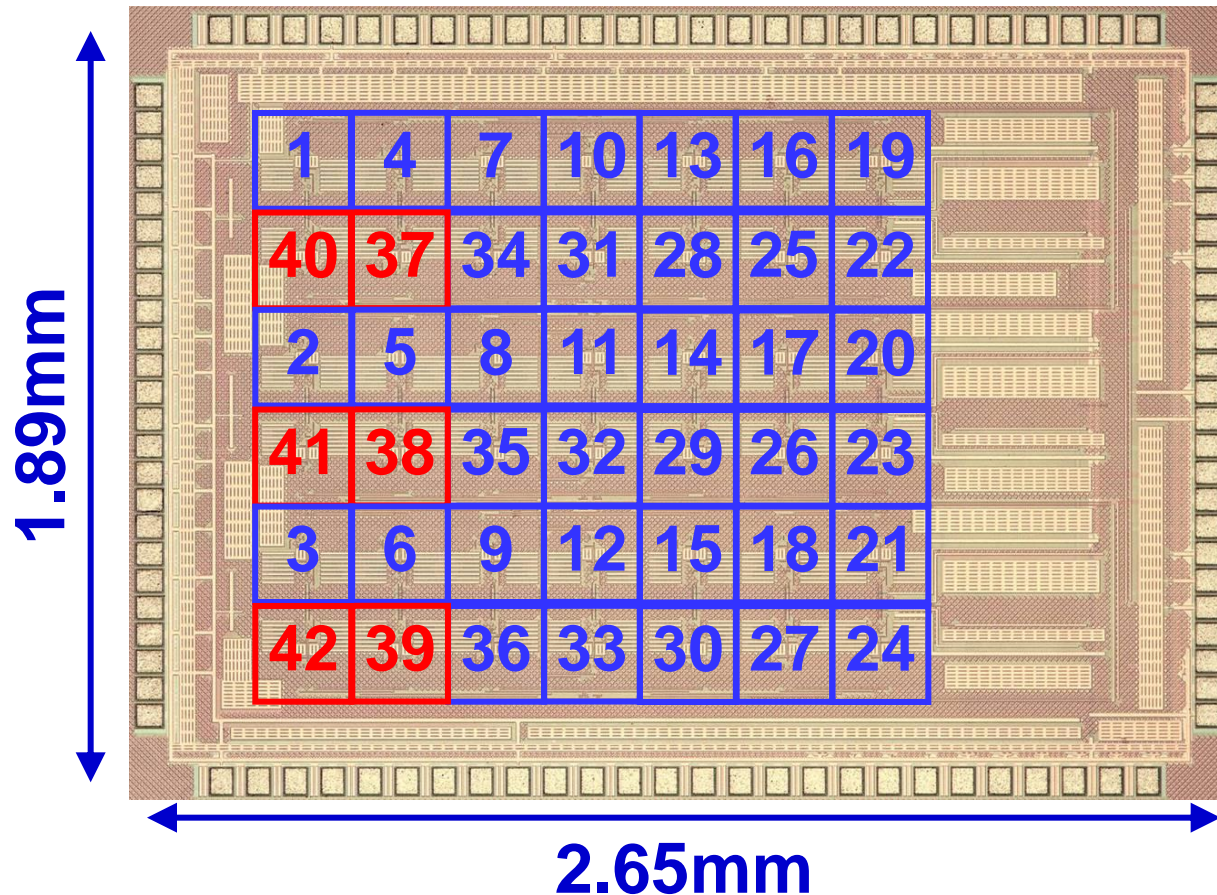


Longer settling time with minimal crosstalk on input and  $V_{sgnd}$



# Chip Implementation

## 65nm CMOS



**Power at  
250MS/s**

**1.17mA at 0.8V**

**+ 0.2mA at 1.2V  
(sampling)**

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**1.20mW total**

# Measured FFT ( $f_{in} = 117\text{MHz}$ )

SNDR = 28.4dB

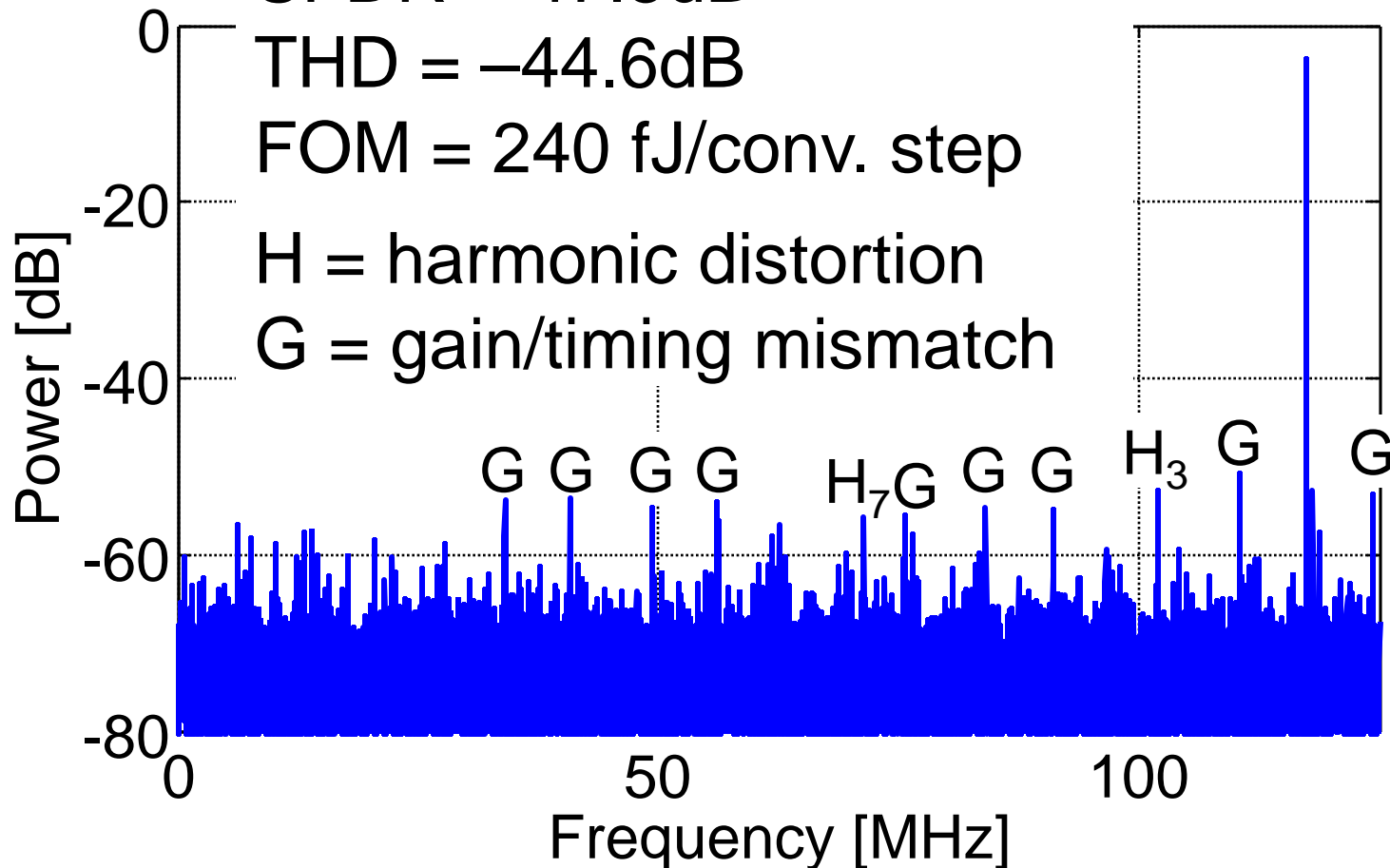
SFDR = 47.5dB

THD = -44.6dB

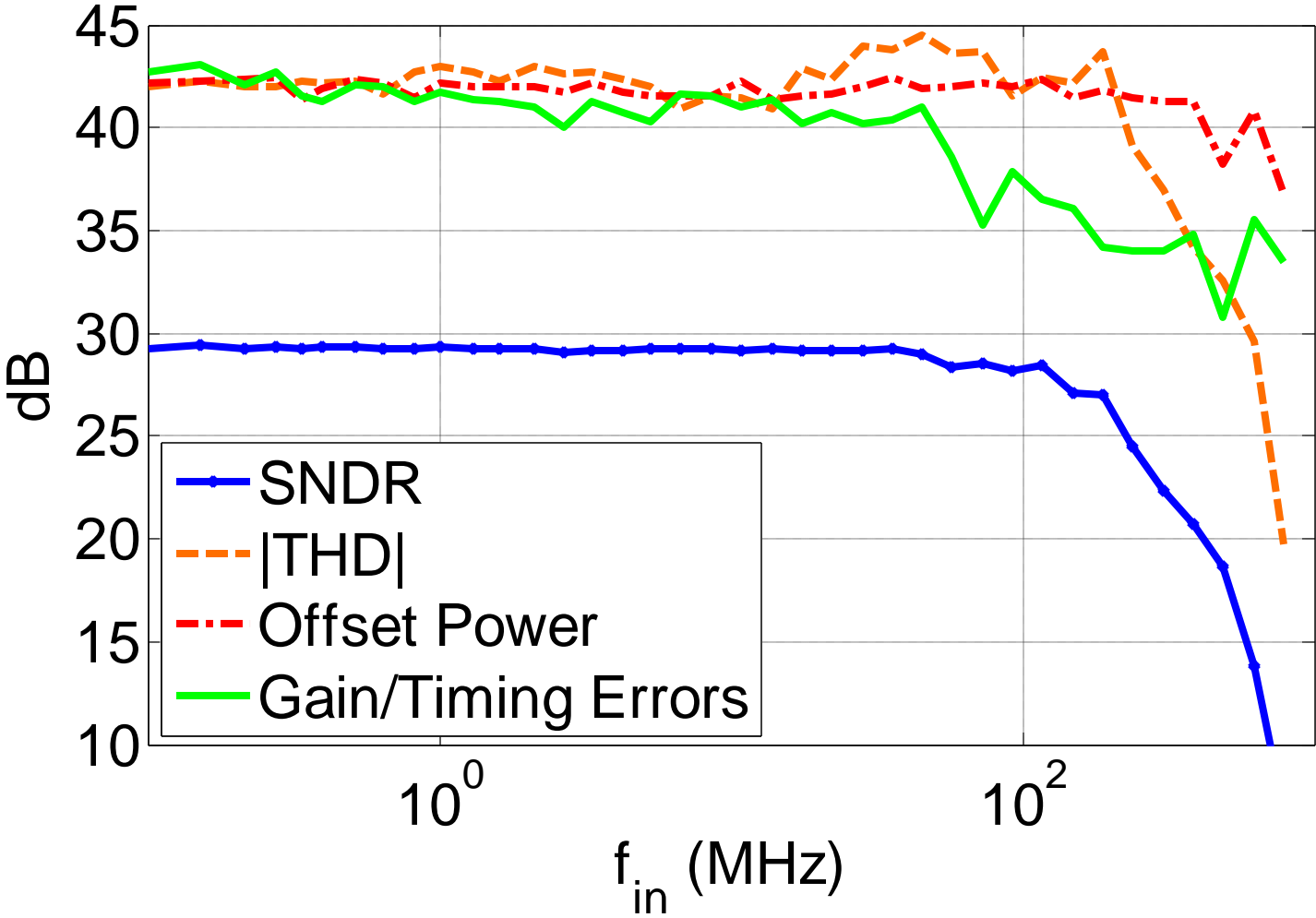
FOM = 240 fJ/conv. step

H = harmonic distortion

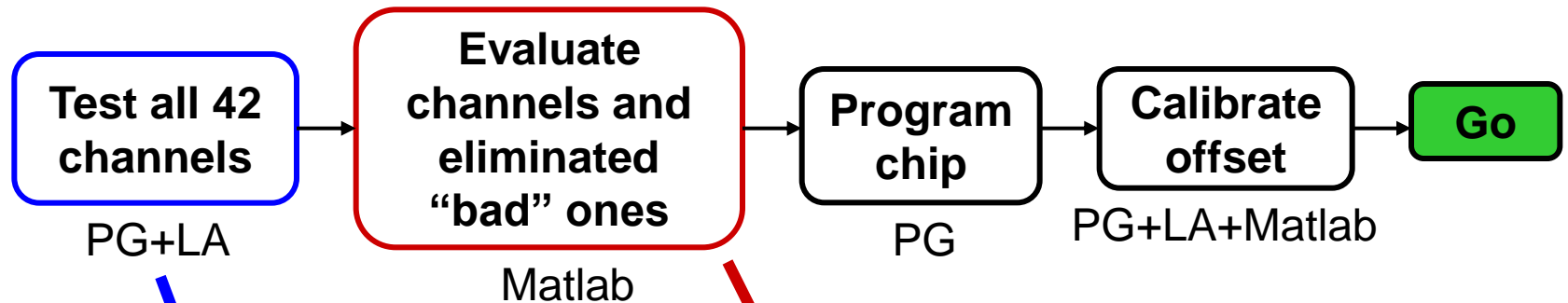
G = gain/timing mismatch



# Measured Dynamic Performance



# Channel Selection Overview

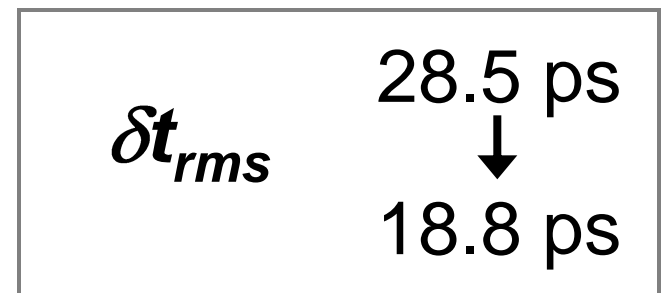
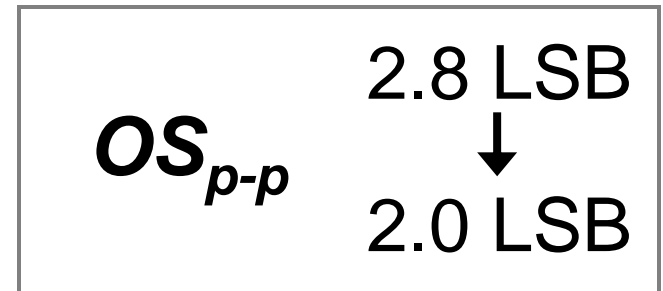
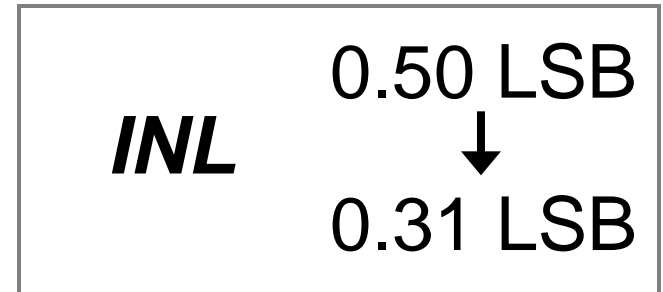
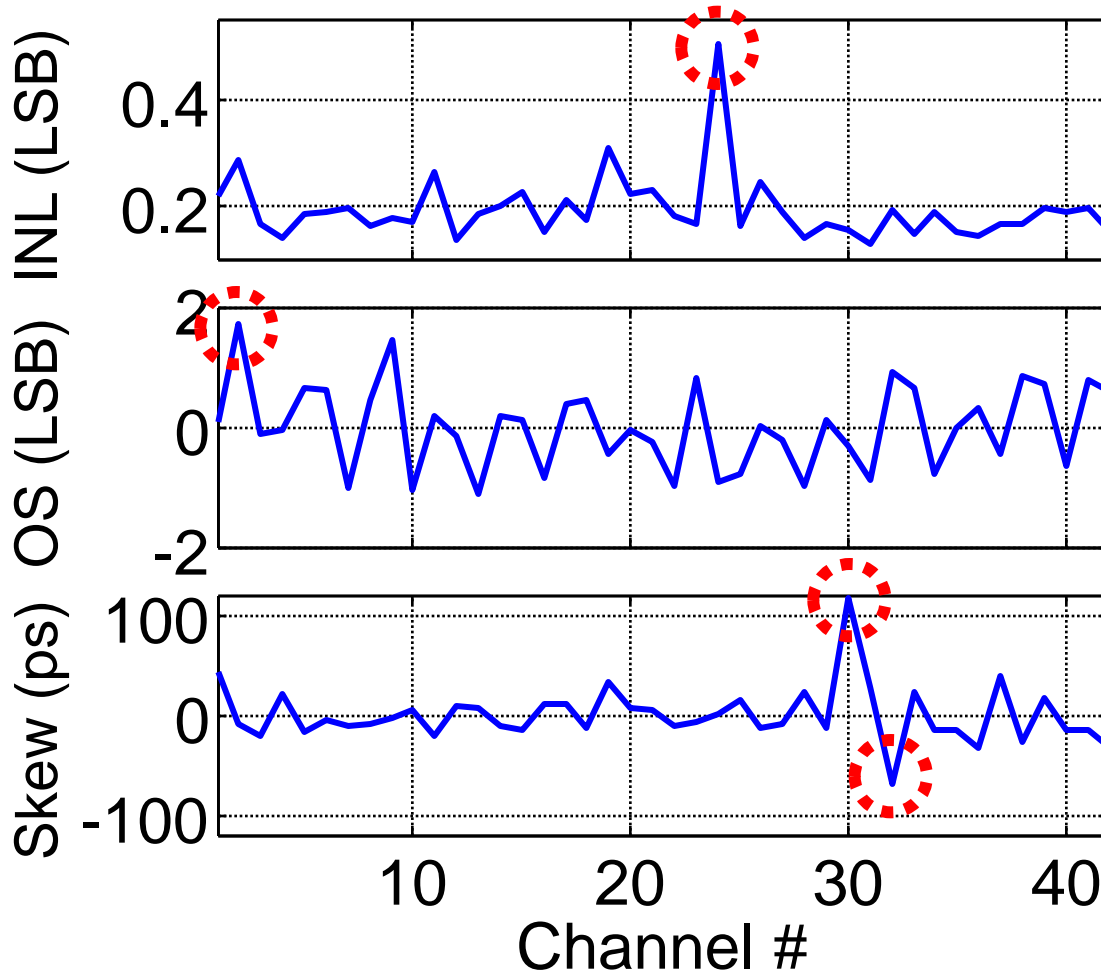


## 4 tests

- Chs. 1-36 (low-F)
- Chs. 1-36 (high-F)
- Chs. 7-42 (low-F)
- Chs. 7-42 (high-F)

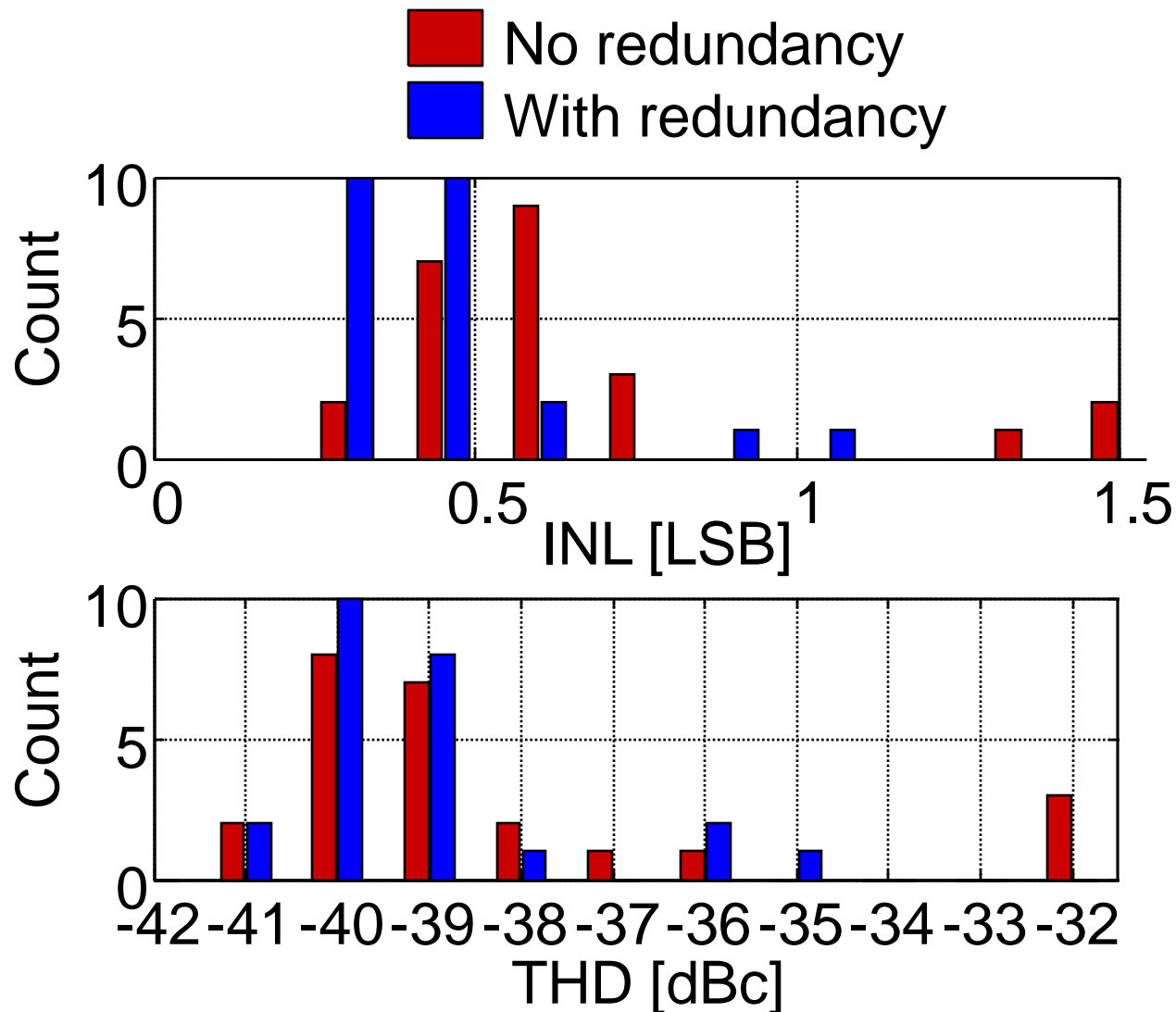
1. Calculate per-channel INL, DNL, SNDR, THD, gain, OS, skew.
2. Assess penalties for marginal/out-of-spec channels.
3. Iteratively eliminate channels with highest penalties.

# Channel Selection Example



before/after  
channel selection

# Histograms Across Chips



**Histograms show the worst active channel on the chip**

# Total Yield

Metric	Specification (every channel)	Yielding Chips out of 24	
		No redundancy	With redundancy
INL	$\leq 0.6$ LSB	14	21
Offset	$\leq 2$ LSB	19	24
SNDR	$\geq 27$ dB	19	22
THD	$\leq -33$ dBc	21	24
All Specifications		10	<b>21</b>

**Redundancy improves yield  
from 42% → 88%**



# Conclusions

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- Slower ADCs are more energy efficient due to sub-threshold operation and voltage scaling
- Redundancy is an extremely powerful tool to counteract yield loss from local variation
  - Apply redundancy at the maximum level of parallelism
- Demonstrated a global sampling network with long sampling windows and small crosstalk

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